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Docket No. 740756-2064

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

12203

In re Patent application of:)
Shunpei YAMAZAKI et al.)
Serial No.: 09/437,135)
Filed: November 10, 1999)
For: SEMICONDUCTOR DEVICE AND)
METHOD FOR FORMING THE SAME)

Group Art Unit: 2813
Examiner: E. Kielin

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TECHNOLOGY CENTER 2800

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Responsive to the Office Action dated August 14, 2002, the following amendments and remarks are submitted in connection with the above-identified application.

IN THE CLAIMS:

Please amended claims 1, 6, 11, 30 and 34 as follows. Attached hereto is a marked up copy of the claims in their amended form.

SUB
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1. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:
- forming a semiconductor film comprising amorphous silicon over a substrate;
 - crystallizing said semiconductor film by irradiating a laser light;
 - patterning the crystallized semiconductor film to form first and second semiconductor islands;
 - forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400° C.;